4. A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode comprising a reflecting material and a light-transmitting material over a first substrate; and

a plurality of sensor portions disposed in matrix over a second substrate opposed to said first substrate,

wherein each of said sensor portions has a photo-electric conversion device, and can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

8. A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode comprising a reflecting material and a light-transmitting material over a substrate; and

a plurality of sensor portions arranged in matrix over said substrate, wherein each of said sensor portions has a photo-electric conversion device, and at least a part of said photo-electric conversion device is extended in such a manner as to overlap with said active device.

10. A display device comprising:

a plurality of pixel portions each comprising a transistor and arranged in matrix over a substrate;

a plurality of sensor portions arranged in matrix over said substrate and comprising an upper electrode and a lower electrode and a photoelectric conversion layer provided between said upper electrode and said lower electrode;

an insulation film provided over said upper electrode; and

a pixel electrode provided over said insulation film and connected with one of a source region and a drain region of said transistor;

wherein said pixel electrode overlaps with said upper electrode with said insulation film therebetween to provide a capacitance.

12. A semiconductor device comprising:

a pixel portion having an active device and a pixel electrode comprising a reflecting material and a light-transmitting material over a substrate; and

a sensor portion provided over said substrate and comprising a photo-electric conversion device,

wherein said active device, said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and

wherein said sensor portion can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

15. A semiconductor device comprising:

a first substrate and a second substrate opposed to said first substrate;

a pixel portion having an active device and a pixel electrode comprising a reflecting material and a light-transmitting material over said first substrate; and

a sensor portion provided over said second substrate and comprising a photo-electric conversion device,

wherein said active device, said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and

wherein said sensor portion can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

19. A semiconductor device comprising:

a pixel portion having an active device and a pixel electrode comprising a reflecting material and a light-transmitting material over a substrate; and

a sensor portion provided over said substrate and having a photo-electric conversion device,

wherein said active device, said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and

wherein at least a part of said photo-electric conversion device is extended in such a manner as to overlap with said active device.

21. A semiconductor device comprising:

a pixel portion comprising a transistor provided over a substrate; and

a sensor portion provided over said substrate and comprising an upper electrode and a lower electrode and a photoelectric conversion layer provided between said upper electrode and said lower electrode;

an insulation film provided over said upper electrode; and

a pixel electrode provided over said insulation film and connected with one of a source region and a drain region of said transistor;

wherein said pixel electrode overlaps with said upper electrode with said insulation film therebetween to provide a capacitance.

Please add new claims as follows.

--23. A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode comprising a reflecting part and a light-transmitting part over a substrate; and

a plurality of sensor portions arranged in matrix over said substrate,

wherein each of said sensor portions includes a photo-electric conversion device, and can read information by utilizing the rays of light transmitting through said light-transmitting part when an external image is read.

24. A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode comprising a reflecting part and a light-transmitting part over a first substrate; and

a plurality of sensor portions disposed in matrix over a second substrate opposed to said first substrate,

wherein each of said sensor portions has a photo-electric conversion device, and can read information by utilizing the rays of light transmitting through said light-transmitting part when an external image is read.

25. A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode comprising a reflecting part and a light-transmitting part over a substrate; and

a plurality of sensor portions arranged in matrix over said substrate, wherein each of said sensor portions has a photo-electric conversion device, and at least a part of said photo-electric conversion device is extended in such a manner as to overlap with said active device.

26. A semiconductor device comprising:

a pixel portion having an active device and a pixel electrode comprising a reflecting part and a light-transmitting part over a substrate; and

a sensor portion provided over said substrate and comprising a photo-electric conversion device,

wherein said active device, said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and

wherein said sensor portion can read information by utilizing the rays of light transmitting through said light-transmitting part when an external image is read.

27. A semiconductor device comprising:

a first substrate and a second substrate opposed to said first substrate;

a pixel portion having an active device and a pixel electrode comprising a reflecting part and a light-transmitting part over said first substrate; and

a sensor portion provided over said second substrate and comprising a photo-electric conversion device,

wherein said active device, said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and

wherein said sensor portion can read information by utilizing the rays of light transmitting through said light-transmitting part when an external image is read.

28. A semiconductor device comprising:

a pixel portion having an active device and a pixel electrode comprising a reflecting part and a light-transmitting part over a substrate; and

a sensor portion provided over said substrate and having a photo-electric conversion device,

wherein said active device, said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and

wherein at least a part of said photo-electric conversion device is extended in such a manner as to overlap with said active device.--